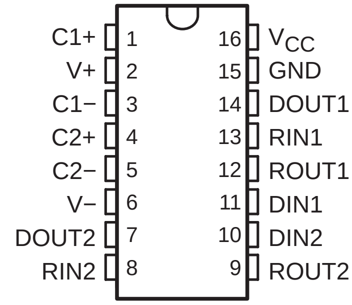
- **RS-232 Bus-Pin ESD Protection Exceeds ±15 kV Using Human-Body Model (HBM)**
- **Meets or Exceeds the Requirements of TIA/EIA-232-F and ITU v.28 Standards**
- **Operates With 3-V to 5.5-V V_{CC} Supply**
- **Operates Up To 250 kbit/s**
- **Two Drivers and Two Receivers**
- **Low Supply Current . . . 300 µA Typical**
- **External Capacitors . . . 4 × 0.1 µF**
- **Accepts 5-V Logic Input With 3.3-V Supply**
- **Alternative High-Speed Pin-Compatible Device (1 Mbit/s) MAX3232**
- **Applications**
  - **Battery-Powered Systems, PDAs, Notebooks, Laptops, Palmtop PCs, and Hand-Held Equipment**

D, DB, DW, OR PW PACKAGE (TOP VIEW)



SOP-16

ORDERING INFORMATION

T_A	PACKAGE†		TOP-SIDE MARKING
−0°C to 70°C	SOIC (CDR)	Tube of 40	MAX3232
		Reel of 2500	
	SOIC (DW)	Tube of 40	
		Reel of 2000	
	SSOP (DB)	Tube of 80	MAX3232DB
		Reel of 2000	
	TSSOP (PW)	Tube of 90	
		Reel of 2000	
−40°C to 85°C	SOIC (CDR)	Tube of 40	MAX3232I
		Reel of 2500	
	SOIC (DW)	Tube of 40	
		Reel of 2000	
	SSOP (DB)	Tube of 80	MAX3232IP
		Reel of 2000	
	TSSOP (PW)	Tube of 90	
		Reel of 2000	

The MAX3232 device consists of two line drivers, two line receivers, and a dual charge-pump circuit with ±15-kV ESD protection pin to pin (serial-port connection pins, including GND). The device meets the requirements of TIA/EIA-232-F and provides the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The devices operate at data signaling rates up to 250 kbit/s and a maximum of 30-V/µs driver output slew rate.

Function Tables

EACH DRIVER

INPUT DIN	OUTPUT DOUT
L	H
H	L

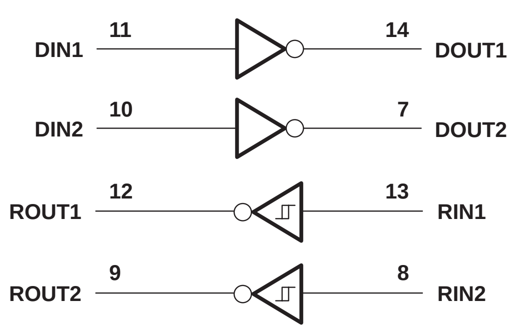
H = high level, L = low level

EACH RECEIVER

INPUT RIN	OUTPUT ROUT
L	H
H	L
Open	H

H = high level, L = low level, Open = input disconnected or connected driver off

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} (see Note 1) . . . . . −0.3 V to 6 V
Positive output supply voltage range, V+ (see Note 1) . . . . . −0.3 V to 7 V
Negative output supply voltage range, V− (see Note 1) . . . . . 0.3 V to −7 V
Supply voltage difference, V+ − V− (see Note 1) . . . . . 13 V
Input voltage range, V_I: Drivers . . . . . −0.3 V to 6 V
Receivers . . . . . −25 V to 25 V
Output voltage range, V_O: Drivers . . . . . −13.2 V to 13.2 V
Receivers . . . . . −0.3 V to V_{CC} + 0.3 V
Package thermal impedance, θ_{JA} (see Notes 2 and 3): CDR package . . . . . 73°C/W
DB package . . . . . 82°C/W
DW package . . . . . 57°C/W
PW package . . . . . 108°C/W
Operating virtual junction temperature, T_J . . . . . 150°C
Storage temperature range, T_{stg} . . . . . −65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltages are with respect to network GND.
2. Maximum power dissipation is a function of T_J(max), θ_{JA}, and T_A. The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) - T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.
3. The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions (see Note 4 and Figure 4)

				MIN	NOM	MAX	UNIT
	Supply voltage		V_{CC} = 3.3 V	3	3.3	3.6	V
			V_{CC} = 5 V	4.5	5	5.5	
V_{IH}	Driver high-level input voltage	DIN	V_{CC} = 3.3 V	2			V
			V_{CC} = 5 V	2.4			
V_{IL}	Driver low-level input voltage		DIN			0.8	V
V_I	Driver input voltage		DIN	0		5.5	V
	Receiver input voltage			−25		25	
T_A	Operating free-air temperature		MAX3232	0		70	°C
				−40		85	

NOTE 4: Test conditions are C1−C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2−C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 4)

PARAMETER		TEST CONDITIONS	MIN	TYP‡	MAX	UNIT
I_{CC}	Supply current	No load, V_{CC} = 3.3 V or 5 V		0.3	1	mA

‡ All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
NOTE 4: Test conditions are C1−C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2−C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

DRIVER SECTION

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 4)

PARAMETER		TEST CONDITIONS		MIN	TYP†	MAX	UNIT
V_{OH}	High-level output voltage	DOUT at R_L = 3 kΩ to GND,	DIN = GND	5	5.4		V
V_{OL}	Low-level output voltage	DOUT at R_L = 3 kΩ to GND,	DIN = V_{CC}	−5	−5.4		V
I_{IH}	High-level input current	$V_I = V_{CC}$			±0.01	±1	µA
I_{IL}	Low-level input current	V_I at GND			±0.01	±1	µA
I_{OS}‡	Short-circuit output current	V_{CC} = 3.6 V,	V_O = 0 V		±35	±60	mA
		V_{CC} = 5.5 V,	V_O = 0 V				
r_o	Output resistance	V_{CC}, V+, and V− = 0 V,	V_O = ±2 V	300	10M		Ω

† All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
‡ Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one output should be shorted at a time.
NOTE 4: Test conditions are C1−C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2−C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 4)

PARAMETER		TEST CONDITIONS		MIN	TYP†	MAX	UNIT
	Maximum data rate	C_L = 1000 pF, One DOUT switching,	R_L = 3 kΩ, See Figure 1	150	250		kbit/s
$t_{sk(p)}$	Pulse skew§	C_L = 150 pF to 2500 pF	R_L = 3 kΩ to 7 kΩ, See Figure 2		300		ns
SR(tr)	Slew rate, transition region (see Figure 1)	R_L = 3 kΩ to 7 kΩ, V_{CC} = 3.3 V	C_L = 150 pF to 1000 pF	6		30	V/µs
			C_L = 150 pF to 2500 pF	4		30	

† All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
§ Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device.
NOTE 4: Test conditions are C1−C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2−C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

RECEIVER SECTION

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 4)

PARAMETER		TEST CONDITIONS	MIN	TYP†	MAX	UNIT
V_{OH}	High-level output voltage	I_{OH} = −1 mA	V_{CC}−0.6 V	V_{CC}−0.1 V		V
V_{OL}	Low-level output voltage	I_{OL} = 1.6 mA			0.4	V
V_{IT+}	Positive-going input threshold voltage	V_{CC} = 3.3 V		1.5	2.4	V
		V_{CC} = 5 V		1.8	2.4	
V_{IT-}	Negative-going input threshold voltage	V_{CC} = 3.3 V	0.6	1.2		V
		V_{CC} = 5 V	0.8	1.5		
V_{hys}	Input hysteresis (V_{IT+} − V_{IT-})			0.3		V
r_i	Input resistance	V_I = ±3 V to ±25 V	3	5	7	kΩ

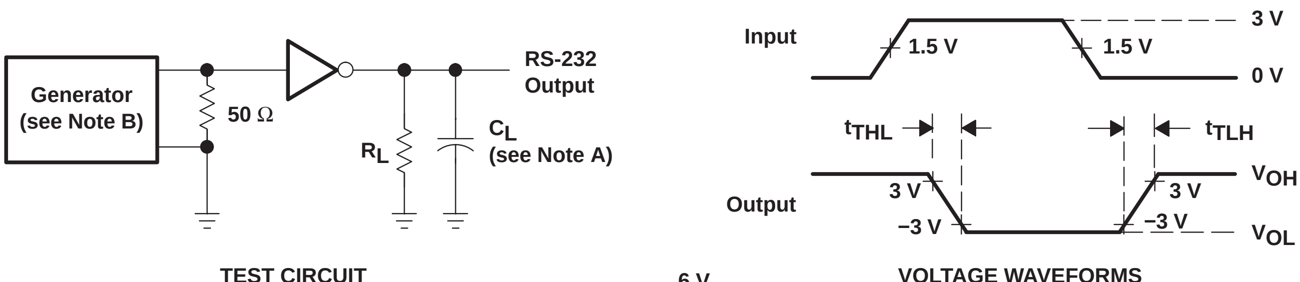
† All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
NOTE 4: Test conditions are C1−C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2−C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 3)

PARAMETER		TEST CONDITIONS	MIN	TYP†	MAX	UNIT
t_{PLH}	Propagation delay time, low- to high-level output	C_L = 150 pF		300		ns
t_{PHL}	Propagation delay time, high- to low-level output			300		ns
$t_{sk(p)}$	Pulse skew‡			300		ns

† All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
‡ Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device.
NOTE 4: Test conditions are C1−C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2−C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

PARAMETER MEASUREMENT INFORMATION

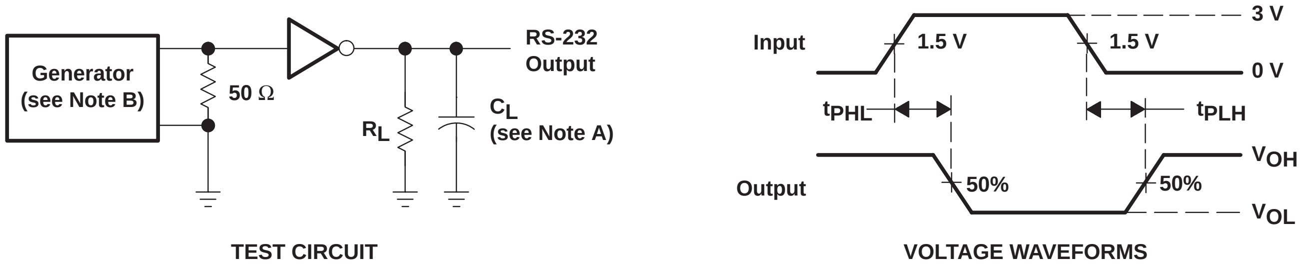


$$SR(tr) = \frac{6\ V}{t_{THL} \text{ or } t_{TLH}}$$

NOTES: A. C_L includes probe and jig capacitance.
B. The pulse generator has the following characteristics: PRR = 250 kbit/s, Z_O = 50 Ω, 50% duty cycle, t_r ≤ 10 ns, t_f ≤ 10 ns.

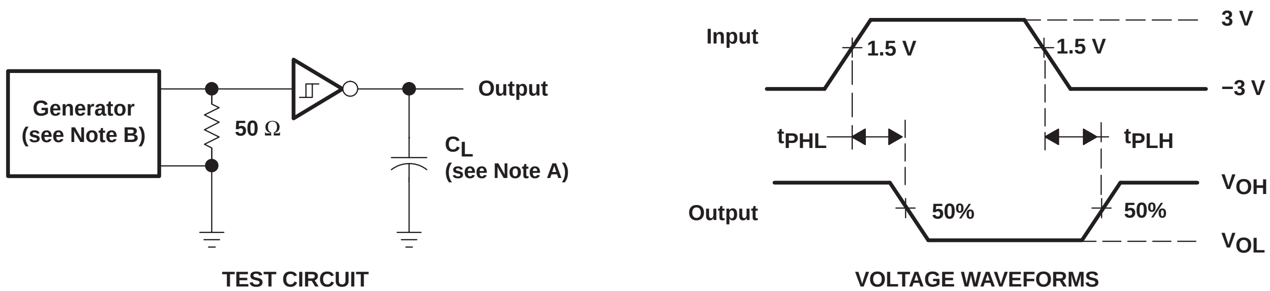
Figure 1. Driver Slew Rate

PARAMETER MEASUREMENT INFORMATION



NOTES: A. C_L includes probe and jig capacitance.
B. The pulse generator has the following characteristics: PRR = 250 kbit/s, Z_O = 50 Ω, 50% duty cycle, $t_r \leq 10$ ns, $t_f \leq 10$ ns.

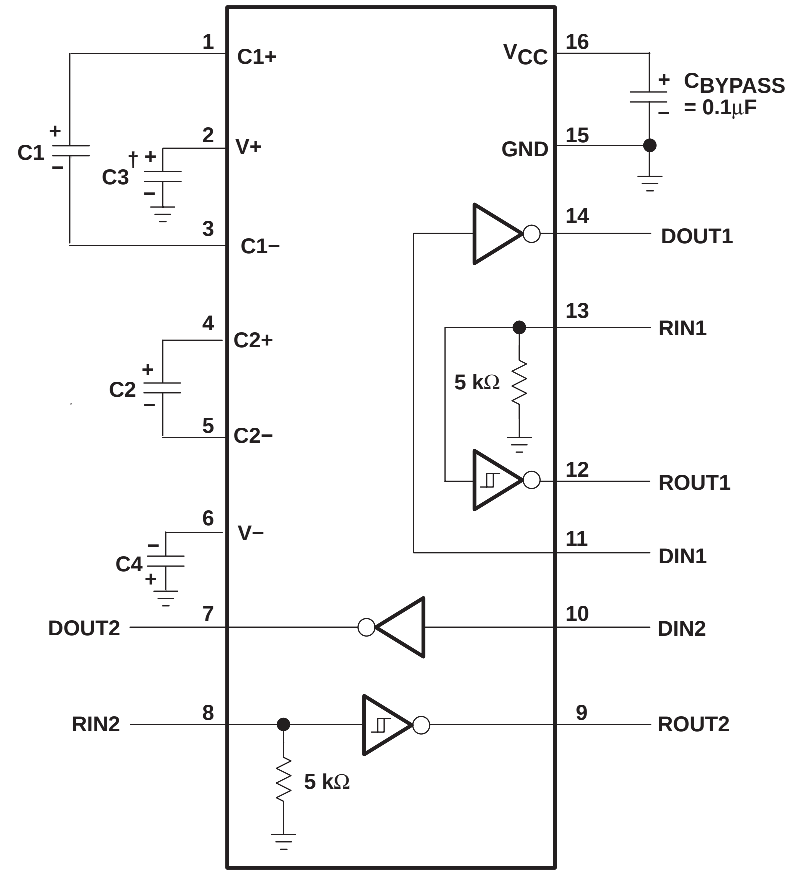
Figure 2. Driver Pulse Skew



NOTES: A. C_L includes probe and jig capacitance.
B. The pulse generator has the following characteristics: Z_O = 50 Ω, 50% duty cycle, $t_r \leq 10$ ns, $t_f \leq 10$ ns.

Figure 3. Receiver Propagation Delay Times

APPLICATION INFORMATION



† C3 can be connected to V_{CC} or GND.

NOTES: A. Resistor values shown are nominal.

B. Nonpolarized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.

V_{CC} vs CAPACITOR VALUES

V_{CC}	C1	C2, C3, C4
3.3 V ± 0.3 V	0.1 μF	0.1 μF
5 V ± 0.5 V	0.047 μF	0.33 μF
3 V to 5.5 V	0.1 μF	0.47 μF

Figure 4. Typical Operating Circuit and Capacitor Values